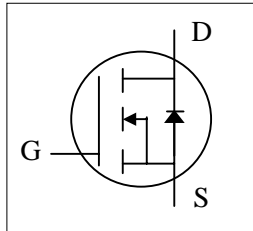




- ▼ Simple Drive Requirement
- ▼ Low Gate Charge
- ▼ Fast Switching

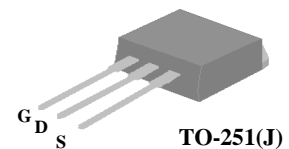
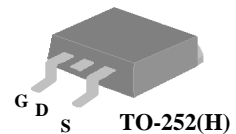


$BV_{DSS}$	30V
$R_{DS(ON)}$	25m $\Omega$
$I_D$	28A

## Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-252 package is widely preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters. The through-hole version (AP40T03GJ) are available for low-profile applications.



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	+25	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V	28	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V	24	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	95	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation	31.25	W
	Linear Derating Factor	0.25	W/ $^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

## Thermal Data

Symbol	Parameter	Value	Units
$R_{thj-c}$	Maximum Thermal Resistance, Junction-case	4	$^\circ\text{C}/\text{W}$
$R_{thj-a}$	Maximum Thermal Resistance, Junction-ambient (PCB mount) <sup>3</sup>	62.5	$^\circ\text{C}/\text{W}$
$R_{thj-a}$	Maximum Thermal Resistance, Junction-ambient	110	$^\circ\text{C}/\text{W}$



# AP40T03GH/J

## Electrical Characteristics @T<sub>j</sub>=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	-	-	V
ΔBV <sub>DSS</sub> /ΔT <sub>j</sub>	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	-	0.032	-	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =18A	-	-	25	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =14A	-	-	45	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1	-	3	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =18A	-	20	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V	-	-	1	uA
	Drain-Source Leakage Current (T <sub>j</sub> =150°C)	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V	-	-	25	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> = ±25V	-	-	±100	nA
Q <sub>g</sub>	Total Gate Charge <sup>2</sup>	I <sub>D</sub> =18A	-	8.8	-	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =20V	-	2.5	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =4.5V	-	5.8	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time <sup>2</sup>	V <sub>DS</sub> =15V	-	6	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =18A	-	62	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =3.3Ω, V <sub>GS</sub> =10V	-	16	-	ns
t <sub>f</sub>	Fall Time	R <sub>D</sub> =0.83Ω	-	4.4	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	655	-	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =25V	-	145	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	95	-	pF

## Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I <sub>S</sub>	Continuous Source Current ( Body Diode )	V <sub>D</sub> =V <sub>G</sub> =0V, V <sub>S</sub> =1.3V	-	-	28	A
I <sub>SM</sub>	Pulsed Source Current ( Body Diode ) <sup>1</sup>		-	-	95	A
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	T <sub>j</sub> =25°C, I <sub>S</sub> =28A, V <sub>GS</sub> =0V	-	-	1.3	V

### Notes:

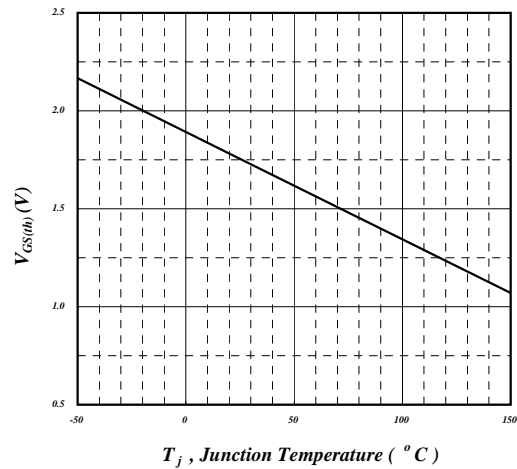
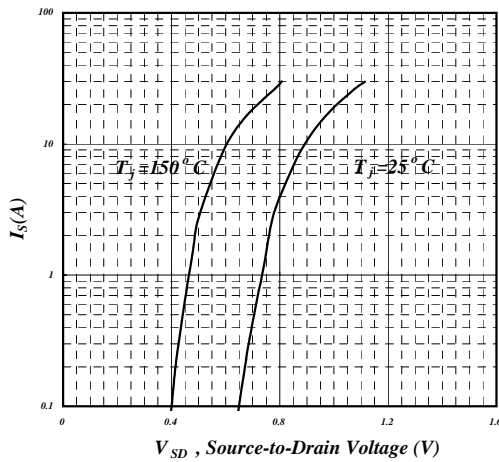
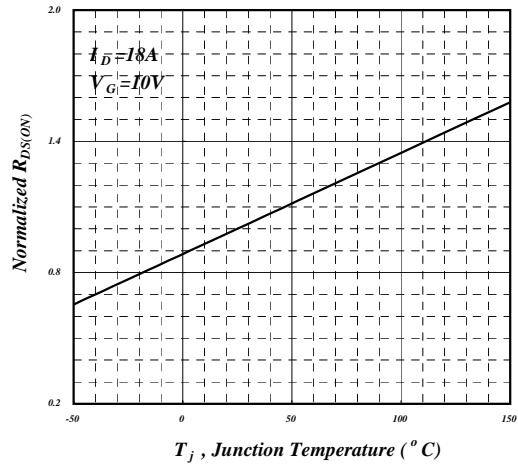
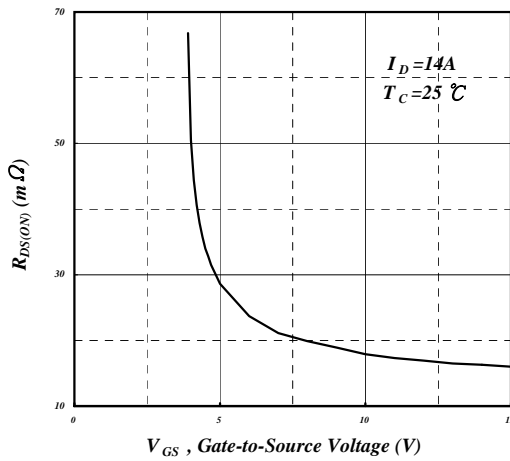
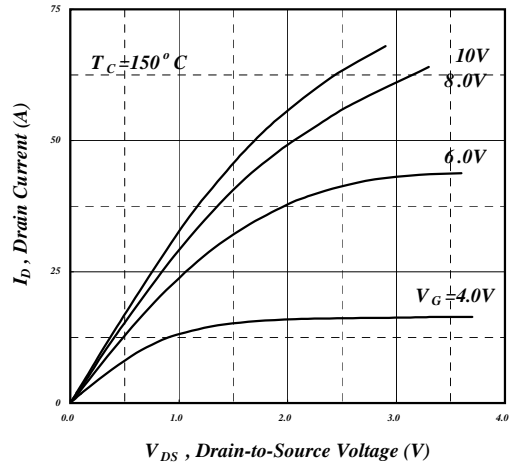
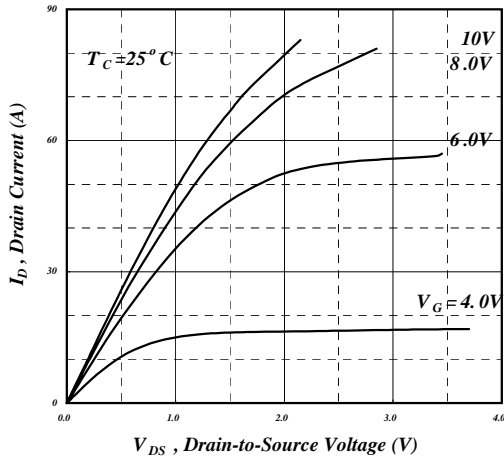
- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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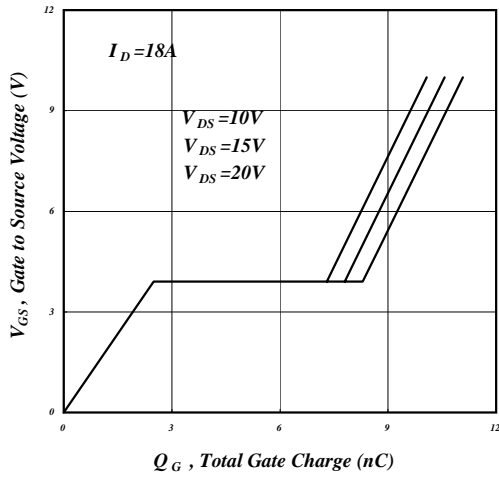


Fig 7. Gate Charge Characteristics

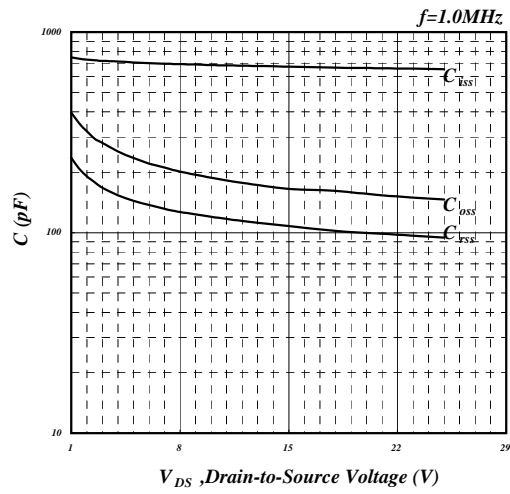


Fig 8. Typical Capacitance Characteristics

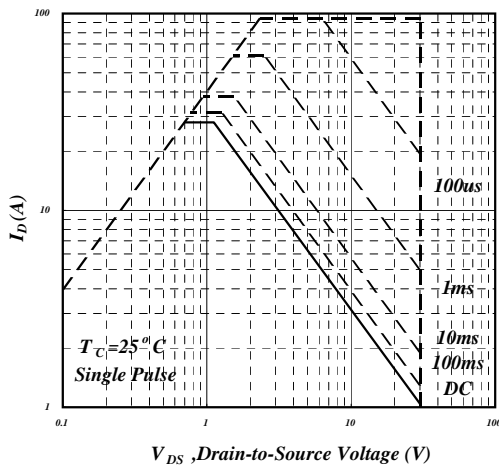


Fig 9. Maximum Safe Operating Area

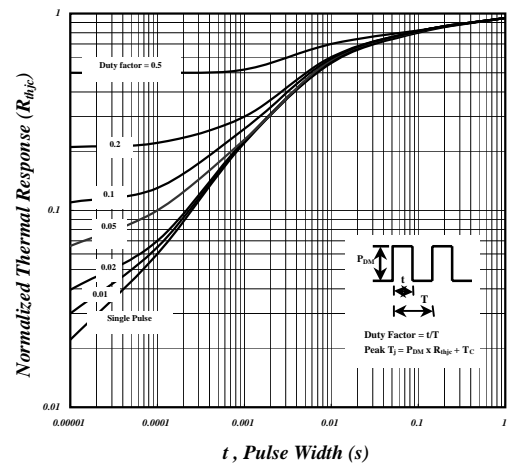


Fig 10. Effective Transient Thermal Impedance

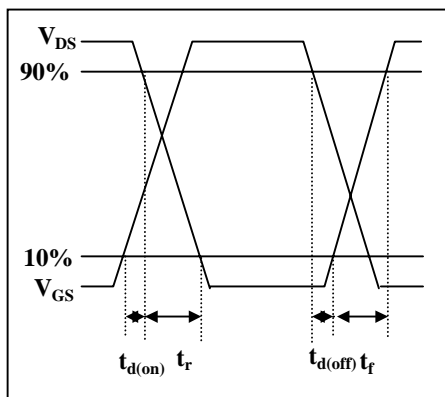


Fig 11. Switching Time Waveform

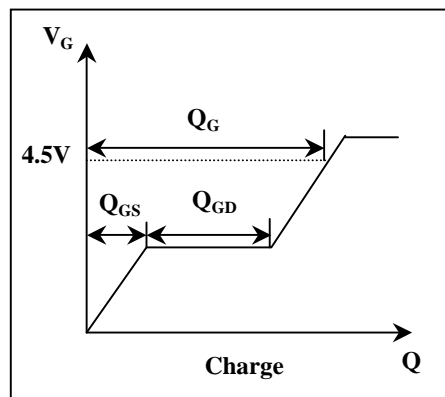


Fig 12. Gate Charge Waveform

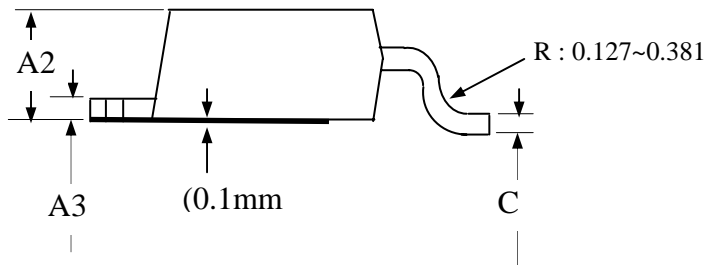


Package Outline : TO-252



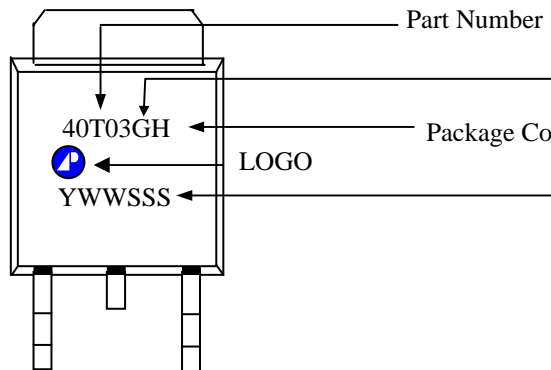
SYMBOLS	Millimeters		
	MIN	NOM	MAX
A2	1.80	2.30	2.80
A3	0.40	0.50	0.60
B1	0.40	0.70	1.00
D	6.00	6.50	7.00
D1	4.80	5.35	5.90
E3	3.50	4.00	4.50
F	2.20	2.63	3.05
F1	0.50	0.85	1.20
E1	5.10	5.70	6.30
E2	0.50	1.10	1.80
e	--	2.30	--
C	0.35	0.50	0.65

- 1.All Dimensions Are in Millimeters.
- 2.Dimension Does Not Include Mold Protrusions.



Part Marking Information & Packing : TO-252

Laser Marking



Meet Rohs requirement for low voltage MOSFET only

Date Code (YWWSSS)

Y : Last Digit Of The Year

WW : Week

SSS : Sequence



Package Outline : TO-251



Part Marking Information & Packing : TO-251

